

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 7, line 3, and extending to page 8, line 5, with the following replacement paragraph:

The edge moving sensitivity DM will be explained below. Exposure dose for forming a photo resist pattern having a desired proper dimension (target dimension), when a mask pattern having a desired proper dimension (target dimension) is transferred (projected) to the photo resist, is determined as a proper (appropriate) exposure dose. In other words, exposure is carried out with proper exposure dose using the mask pattern having the proper dimension, and thereby, photo resist pattern having proper dimension is obtained. However, mask pattern having a dimension deviating from the proper dimension may be manufactured. In such a case, exposure is carried out with exposure dose deviating from the proper exposure dose, and thereby, resist pattern having a proper dimension can be formed. The relationship between Δm (corresponding to mask edge moving amount m) and ΔE changes in accordance with pattern. The Δm represents a deviation from the proper dimension of the mask pattern, and the ΔE represents a deviation from the proper exposure dose to be set in accordance with the shift Δm . Therefore, the relationship between the deviations ΔE and Δm is a significant factor to extract dangerous pattern. Thus, the edge moving sensitivity DM corresponding to $\Delta E/\Delta m$ is used as the index, and the upper limit value DM_{max} of the edge moving sensitivity DM and the lower limit value DM_{min} thereof are set in step S5. Incidentally, the edge moving sensitivity DM may be called Dose MEF (mask error enhancement factor).